

N-channel 60 V 14.8 mΩ standard level MOSFET

Rev. 3 — 23 June 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- 1.3 Applications
 - DC-to-DC converters
 - Load switching

- Suitable for standard level gate drive sources
- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see Figure 1	-	-	50	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	86	W
Tj	junction temperature		-55	-	175	°C
Static ch	aracteristics					
R_{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A}; \\ T_{j} = 100 \ ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12} \end{array}$	-	-	23.7	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	12.6	14.8	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$	-	4.7	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	20.9	-	nC
Avalanc	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 50 \text{ A}; \ V_{sup} \leq 60 \text{ V}; \\ R_{GS} = 50 \ \Omega; \ unclamped \end{array} $	-	-	44	mJ

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

3. Ordering information

Table 3.Ordering information

Type number	Package			
	Name	Description	Version	
PSMN015-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

SOT78 (TO-220AB)

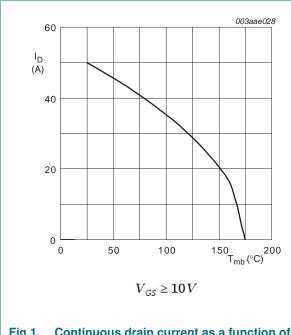
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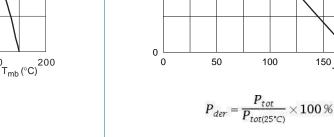
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	-	36	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	-	50	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	201	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	86	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	50	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	201	А
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{D} = 50 \text{ A}; \\ V_{sup} \leq 60 \text{ V}; \text{R}_{GS} = 50 \Omega; \text{ unclamped} \end{array} $	-	44	mJ



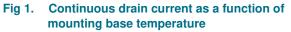


120

80

40

P_{der} (%)



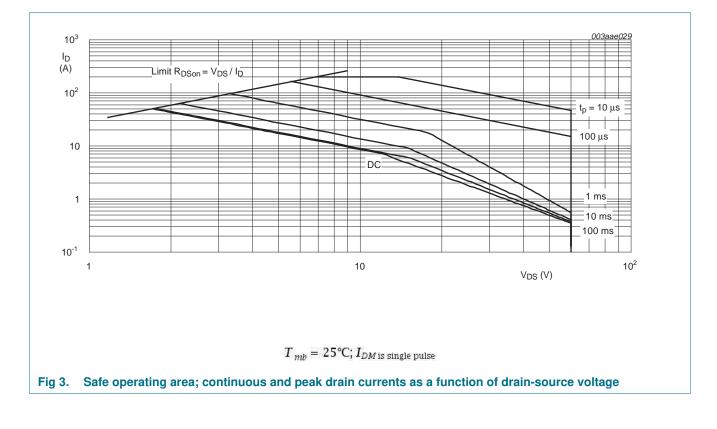


03aa16

150 200 T_{mb} (°C)

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5. Thermal characteristics

Parameter thermal resistance from junction to mounting	Conditions see Figure 4	Min	Тур	Max	Unit
thermal resistance from junction to mounting	see Figure 4				
base	see <u>rigure 4</u>	-	1	1.74	K/W
thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

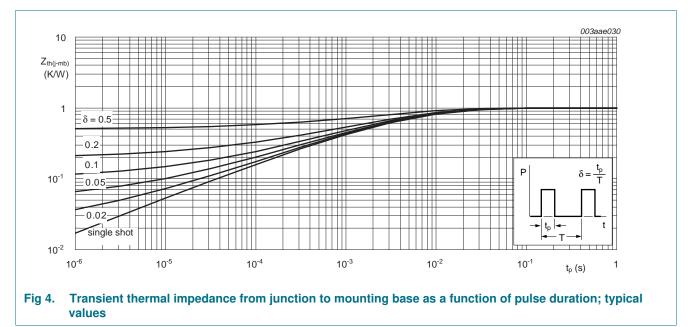


Table 5. Thermal characteristics

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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	54	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V _{GSth}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	4.8	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	0.03	2	μA
		$V_{DS} = 60 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 125 ^{\circ}\text{C}$	-	-	30	μA
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; see <u>Figure 12</u>	-	28.9	34	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	23.7	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see <u>Figure 13</u>	-	12.6	14.8	mΩ
R _G	gate resistance	f = 1 MHz	-	1.3	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	20.9	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{V}; V_{GS} = 10 \text{V}$	-	17	-	nC
Q _{GS}	gate-source charge	I_D = 25 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	6.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; \text{ V}_{DS} = 30 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$ see Figure 14	-	3.7	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.4	-	nC
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.7	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.8	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	1220	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	169	-	pF
C _{rss}	reverse transfer capacitance		-	95	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	12	-	ns
r	rise time	$R_{G(ext)} = 4.7 \ \Omega$	-	13	-	ns
d(off)	turn-off delay time		-	27	-	ns
t _f	fall time		-	7	-	ns

Table 6.

Symbol

Source-drain diode

Characteristics ... continued

Parameter

PSMN015-60PS

Max

Тур

Unit

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Min

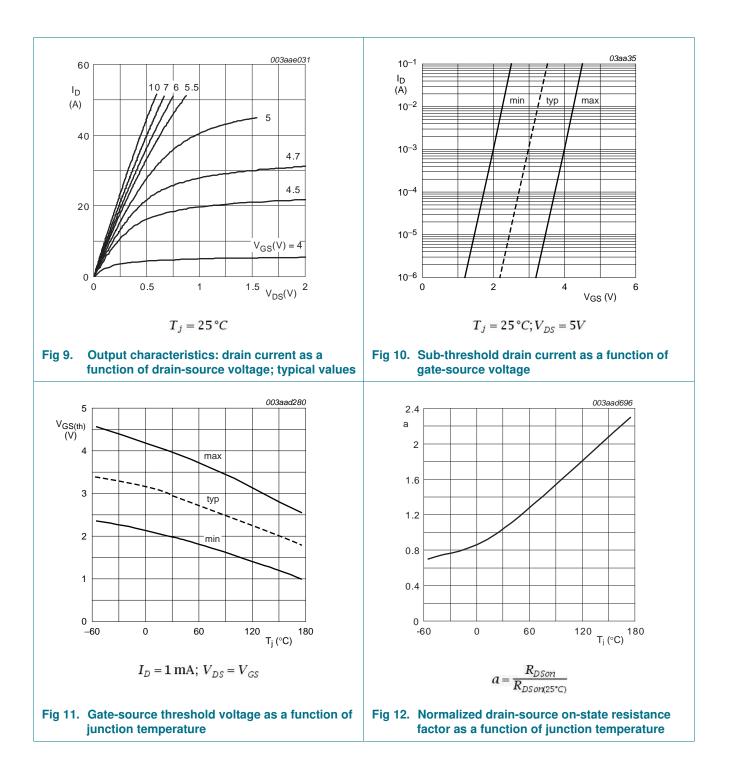
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I_S = 15 A; V_{GS} = 0 V; T_i = 25 °C ٧ source-drain voltage 0.8 V_{SD} 1.2 $I_{\rm S} = 25 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s};$ reverse recovery time 31 ns t_{rr} -- $V_{GS} = 0 V; V_{DS} = 30 V$ Q_r recovered charge 28.5 nC --003aae032 003aae033 50 50 g_{fs} I_D (S) (A) 40 40 30 30 20 20 10 10 T_j = 175 °C T_i = 25 °C 0 0 I_D(A) 50 0 10 20 30 40 0 2 4 6 $V_{GS}(V)$ $T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$ $V_{DS} > I_D \times R_{DSon}$ Forward transconductance as a function of Transfer characteristics: drain current as a Fig 5. Fig 6. drain current; typical values function of gate-source voltage; typical values 003aae035 003aae036 2000 50 R_{DSon} С $(m\Omega)$ (pF) C_{iss} 40 1500 30 Crss 1000 20 500 10 0 0 8 10 V_{GS}(V) 15 _{VGS}(V)²⁰ 2 4 6 5 10 0 0 $V_{DS} = 0V; f = 1MHz$ $T_j = 25 \,^{\circ}C; I_D = 10A$ Fig 7. Input and reverse transfer capacitances as a Fig 8. Drain-source on-state resistance as a function function of gate-source voltage; typical values of gate-source voltage; typical values

Conditions

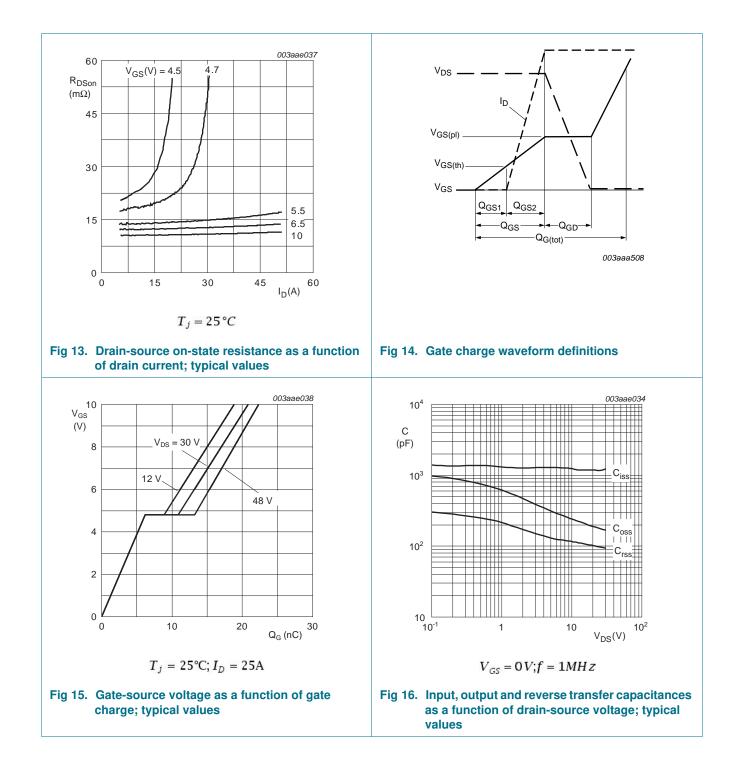
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7. Package outline

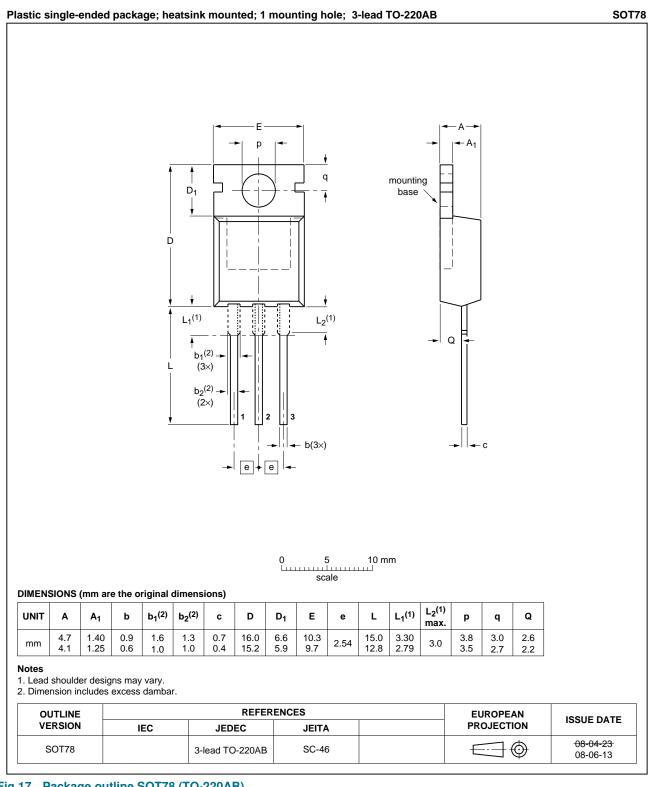


Fig 17. Package outline SOT78 (TO-220AB)

PSMN015-60PS Product data sheet

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN015-60PS v.3	20110623	Product data sheet	-	PSMN015-60PS v.2
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	es to content.		
PSMN015-60PS v.2	20100222	Objective data sheet	-	PSMN015-60PS v.1

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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